

## REMARKS

After entry of this Amendment, claims 68-102 are pending in this application. Claims 68, 69, 89, and 90 are amended and claims 92-102 are added without introduction of new matter. Non-limiting support for the amended and new claims is self-evident or evident from the discussion below.

Claims 68, 90, and 91 stand rejected under 35 U.S.C. 102(e) as being anticipated by U.S. Patent No. 6,312,995 to Yu. This rejection is respectfully traversed.

Claim 68 recites a method of forming a semiconductor transistor, comprising “forming a first gate dielectric over a substrate; forming a first conductive gate region over said first gate dielectric; forming a dielectric layer on the sides of said first conductive gate region; forming a second gate dielectric over said substrate; forming a second conductive gate region over said second gate dielectric, adjacent to said dielectric layer, and on the sides of said first conductive region; and forming source and drain regions in said substrate to define a channel region between them and beneath said first and second conductive type gate regions, wherein all portions of said first gate dielectric, first conductive gate region, second gate dielectric, and second conductive gate region are wholly between said source and drain regions.”

Claim 90 recites a method of forming a semiconductor transistor, comprising “providing a substrate; forming a first gate dielectric layer over said substrate; forming a first gate electrode over said first gate dielectric layer, said first gate electrode having a first workfunction and sidewalls; forming a dielectric layer on the sidewalls of said first gate electrode; forming a second gate dielectric layer over said substrate; forming a pair of second gate electrodes over said second gate dielectric and adjacent to said dielectric layer, said second gate electrodes being separated from said first gate electrode by said dielectric

layer, said pair of second gate electrodes having a second workfunction which is different than said first workfunction; forming a conductive cap over each of said gate electrodes; forming insulating sidewalls adjacent to said conductive cap and said gate electrodes; and forming source and drain regions in said substrate to define a channel region between them and beneath said first and second conductive type gate regions, wherein all portions of said first gate dielectric, first gate electrode, second gate dielectric layer, and pair of second gate electrodes are wholly between said source and drain regions." Claim 91 depends from claim 90.

As can be seen, claim 68 recites "wherein all portions of said first gate dielectric, first conductive gate region, second gate dielectric, and second conductive gate region are wholly between said source and drain regions." Claim 90 similarly recites "wherein all portions of said first gate dielectric layer, first gate electrode, second gate dielectric layer, and pair of second gate electrodes are wholly between said source and drain regions." As shown by Yu's Figures 1 and 3, Yu does not teach these features of claims 68 and 90 because "all portions" of Yu's assisted gates 124 (cited as teaching the second conductive gate region and pair of second gate electrodes of claims 68 and 90, respectively) are not "wholly between" the source and drain, as claimed. Rather, the assisted gates 124 partly overhang the source and drain. Accordingly, Applicants respectfully request that this rejection be withdrawn and the claims allowed.

New claims 92-102 are added by this Amendment. Non-limiting support for each of the new claims is provided at least by Applicants' specification, U.S. Pub. No. 2004/0185630, at paras. 20, 22, 27, 28, and 33. New claims 92-99 are believed to be allowable in view of at least the features emphasized in support of patentability for independent claims 68 and 90. New independent claim 100, and claims 101 and 102 depending

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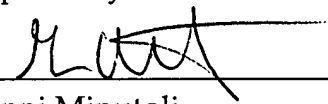
therefrom, are believed to be allowable in view of at least the feature of "forming first and second gate regions capable of being independently biased", which is absent from the cited references.

Claims 69-88 stand objected to as being dependent upon a rejected base claim, but are otherwise allowable. These claims are believed to be allowable in view of at least the features emphasized in support of patentability for independent claim 68.

Applicants believe the pending application is in condition for allowance.

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